

## REMARKS

Claims 1-23 are pending in this patent application. Reconsideration of the rejections in view of the remarks below is requested.

The Office Action rejected claims 1-4, 6-11, 13-18, 20 and 22 under 35 U.S.C. §102(b) as being anticipated by U.S. Patent No. 5,948,219 to Rohner et al. ("Rohner"). Applicant respectfully traverses the rejection, without prejudice.

Applicant respectfully submits that the cited portions of Rohner fail to disclose, teach or suggest a method of fabricating a device using a lithographic process comprising, *inter alia*, exposing a part of a resist layer on a substrate to ultraviolet radiation and applying an electric field across the resist, the direction of the field being substantially perpendicular to a plane of the resist layer during the exposing as recited in claim 1. Similarly, Applicant respectfully submits that the cited portions of Rohner fail to disclose, teach or suggest a method of fabricating a device using a lithographic process, comprising, *inter alia*, exposing a part of the resist to ultraviolet radiation while applying an electric field across the resist as recited in claim 15. Further, Applicant respectfully submits that the cited portions of Rohner fail to disclose, teach or suggest a method of processing a device using a lithographic process, comprising, *inter alia*, exposing the resist material to UV radiation while applying an electric field across the resist material as recited in claim 16.

Specifically, for example, the cited portions of Rohner fail to provide any disclosure, teaching or suggestion regarding applying an electric field across a resist while exposing the resist to UV radiation. The cited portions of Rohner merely discuss photolithography to set up Rohner's lithography device as an alternative to photolithography, namely Rohner's use of an electric field to form features from a desired material upon an upper topography of a semiconductor substrate rather than using photolithography. See, e.g., Rohner, col. 2, lines 5-17 ("It would be beneficial to have a lithography process capable of forming features having physical dimensions smaller than those obtainable using photolithography and at least comparable to photolithography in terms of speed and cost. Such a lithography process would represent an advancement in wafer fabrication technology...The problems outlined above are in large part solved by a lithographic apparatus and method which uses an electric field to form features from a desired material upon an upper topography of a semiconductor substrate.").

Further, Applicant respectfully submits that the cited portions of Rohner fail to disclose, teach or suggest a lithographic apparatus comprising, *inter alia*, an illumination system configured to condition a projection beam of ultraviolet radiation, a projection system configured to project the patterned beam onto a target portion of the substrate and an electric field generator configured and arranged to apply an electric field across a resist layer as recited in claim 14.

As discussed above, the cited portions of Rohner merely disclose a lithography device that is an alternative to photolithography, namely a mechanism using an electric field to form features from a desired material upon an upper topography of a semiconductor substrate instead of photolithography. See, e.g., Rohner, col. 2, lines 5-17. The cited portions of Rohner simply fail to provide any disclosure, teaching or suggestion regarding a combination of an illumination system configured to condition a projection beam of UV radiation, a projection system configured to project the patterned beam of UV radiation and an electric field generator configured and arranged to apply an electric field across a resist layer.

Therefore, for at least the above reasons, the cited portions of Rohner fail to disclose, teach or suggest all the features recited by claims 1, 14, 15 and 16. Claims 2-4, 6-11, 13, 17, 18, 20 and 22 depend from claims 1 and 14-16 respectively and are, therefore, patentable for at least the same reasons provided above regarding claims 1 and 14-16 respectively, and for the additional features recited in those claims. As a result, Applicant respectfully submits that the rejection under 35 U.S.C. §102(b) of claims 1-4, 6-11, 13-18, 20 and 22 in view of Rohner should be withdrawn and the claims allowed.

The Office Action rejected claim 5 under 35 U.S.C. §103(a) as being unpatentable over Rohner. Applicant respectfully traverses the rejection, without prejudice.

As discussed above, the cited portions of Rohner fail to disclose, teach or suggest claim 1. Claim 5 depends from claim 1 and is, therefore, patentable for at least the same reasons provided above regarding claim 1, and for the additional features recited in that claim.

As a result, Applicant respectfully submits that the rejection under 35 U.S.C. §103(a) of claim 5 in view of Rohner should be withdrawn and the claim allowed.

The Office Action rejected claims 12, 19, 21 and 23 under 35 U.S.C. §103(a) as being unpatentable over Rohner in view of U.S. Patent Application Publication No. 2004/0013956 to Sogard ("Sogard"). Applicant respectfully traverses the rejection, without prejudice.

As discussed above, the cited portions of Rohner fail to disclose, teach or suggest claims 1 and 14-16. Claims 12, 19, 21 and 23 depend from claims 1 and 14-16 respectively and are, therefore, patentable for at least the same reasons provided above regarding claims 1 and 14-16 respectively, and for the additional features recited in those claims.

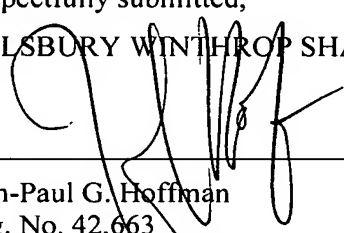
Further, the cited portions of Sogard fail to overcome the deficiencies of Rohner. Sogard merely discloses a system for correcting aberration and distortion in EUV lithography which involves placing a reticle on a deformable reticle chuck, and a reticle height sensor is used to measure the surface height of the reticle placed on the deformable reticle chuck. The reticle is held on the chuck by electrostatic forces. However, for example, the cited portions of Sogard simply have no disclosure, teaching or suggestion regarding applying an electric field across a resist layer or about an electric field generator configured to do so. Further, for example, the cited portions of Sogard have no disclosure regarding applying an electric field across a resist while exposing the resist to UV radiation.

As a result, Applicant respectfully submits that the rejection under 35 U.S.C. §103(a) of claims 12, 19, 21 and 23 as being unpatentable over Rohner in view of Sogard should be withdrawn and the claims allowed.

All rejections having been addressed, it is respectfully submitted that the present application is in condition for allowance. If questions relating to patentability remain, the Examiner is invited to contact the undersigned to discuss them.

Should any fees be due, please charge them to our deposit account no. 03-3975, under our order no. 081468/0309171. The Commissioner for Patents is also authorized to credit any over payments to the above-referenced deposit account.

Respectfully submitted,  
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